

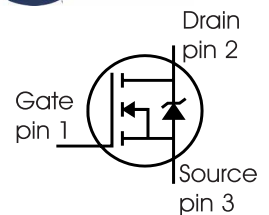
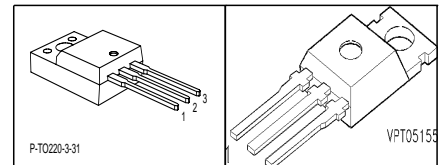
Cool MOS™ Power Transistor

Feature

- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance
- PG-TO-220-3-31: Fully isolated package (2500 VAC; 1 minute)
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁰⁾ for target applications

V_{DS}	800	V
$R_{DS(on)}$	0.29	Ω
I_D	17	A

PG-TO220-3-31 PG-TO220



Type	Package	Ordering Code	Marking
SPP17N80C3	PG-TO220	Q67040-S4353	17N80C3
SPA17N80C3	PG-TO220-3-31	SP000216353	17N80C3

Maximum Ratings

Parameter	Symbol	Value		Unit
		SPP	SPA	
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	I_D	17 11	17 ¹⁾ 11 ¹⁾	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	51	51	A
Avalanche energy, single pulse $I_D=3.4\text{A}$, $V_{DD}=50\text{V}$	E_{AS}	670	670	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ²⁾ $I_D=17\text{A}$, $V_{DD}=50\text{V}$	E_{AR}	0.5	0.5	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	17	17	A
Gate source voltage	V_{GS}	± 20	± 20	V
Gate source voltage AC ($f > 1\text{Hz}$)	V_{GS}	± 30	± 30	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	P_{tot}	208	42	W
Operating and storage temperature	T_j, T_{stg}	-55...+150		$^\circ\text{C}$

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 640 \text{ V}$, $I_D = 17 \text{ A}$, $T_j = 125 \text{ }^\circ\text{C}$	dv/dt	50	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	0.6	K/W
Thermal resistance, junction - case, FullPAK	$R_{thJC \text{ FP}}$	-	-	3.6	
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Thermal resistance, junction - ambient, FullPAK	$R_{thJA \text{ FP}}$	-	-	80	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ³⁾	R_{thJA}	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s ⁴⁾	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$	800	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$, $I_D=17\text{A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=1000\mu\text{A}$, $V_{GS}=V_D$	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=800\text{V}$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.5	25	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=11\text{A}$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.25	0.29	Ω
Gate input resistance	R_G	$f=1\text{MHz}$, open drain	-	0.7	-	

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 11A$	-	15	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	2320	-	pF
Output capacitance	C_{oss}		-	1250	-	
Reverse transfer capacitance	C_{rss}		-	60	-	
Effective output capacitance, ⁵⁾ energy related	$C_{o(er)}$	$V_{GS} = 0V$, $V_{DS} = 0V$ to 480V	-	59	-	
Effective output capacitance, ⁶⁾ time related	$C_{o(tr)}$		-	124	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400V$, $V_{GS} = 0/10V$, $I_D = 17A$, $R_G = 4.7\Omega$, $T_j = 125^\circ C$	-	25	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	82	
Fall time	t_f		-	6	9	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 640V$, $I_D = 17A$	-	12	-	nC
Gate to drain charge	Q_{gd}		-	46	-	
Gate charge total	Q_g	$V_{DD} = 640V$, $I_D = 17A$, $V_{GS} = 0$ to 10V	-	91	177	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640V$, $I_D = 17A$	-	6	-	V

⁰J-STD20 and JESD22

¹Limited only by maximum temperature

²Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

³Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

⁴Soldering temperature for TO-263: 220°C, reflow

⁵ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

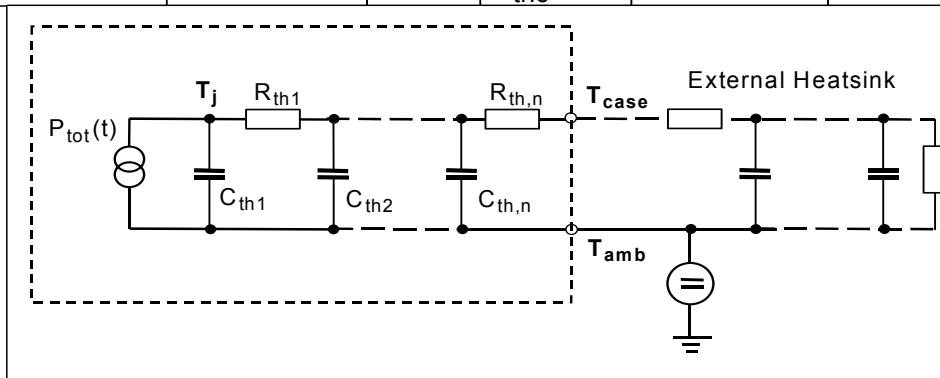
⁶ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	17	A
Inverse diode direct current, pulsed	I_{SM}		-	-	51	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{V}, I_F=I_S,$	-	550	-	ns
Reverse recovery charge	Q_{rr}	$di_F/dt=100\text{A}/\mu\text{s}$	-	15	-	μC
Peak reverse recovery current	I_{rrm}		-	51	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt	$T_j=25^\circ\text{C}$	-	1200	-	$\text{A}/\mu\text{s}$

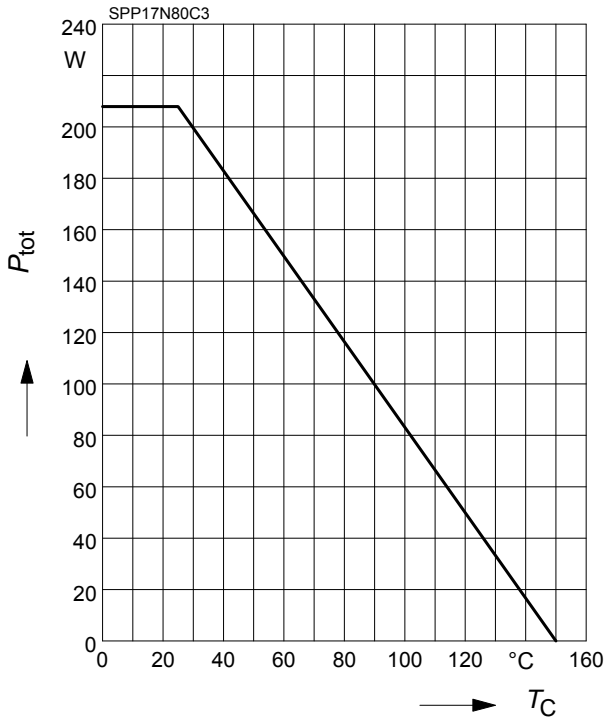
Typical Transient Thermal Characteristics

Symbol	Value		Unit	Symbol	Value		Unit
	SPP	SPA			SPP	SPA	
R_{th1}	0.00812	0.00812	K/W	C_{th1}	0.0003562	0.0003562	Ws/K
R_{th2}	0.016	0.016		C_{th2}	0.001337	0.001337	
R_{th3}	0.031	0.031		C_{th3}	0.001831	0.001831	
R_{th4}	0.114	0.16		C_{th4}	0.005033	0.005033	
R_{th5}	0.135	0.324		C_{th5}	0.012	0.008657	
R_{th6}	0.059	2.522		C_{th6}	0.092	0.412	



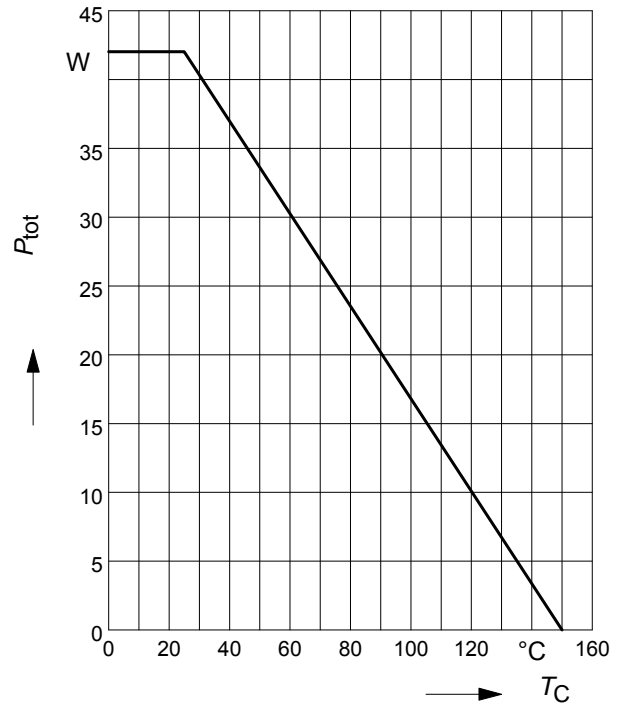
1 Power dissipation

$P_{tot} = f(T_C)$



2 Power dissipation FullPAK

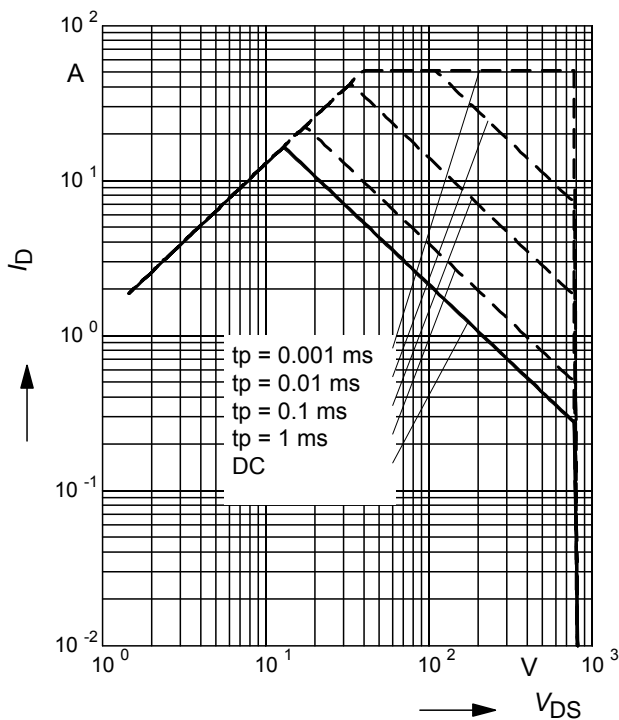
$P_{tot} = f(T_C)$



3 Safe operating area

$I_D = f(V_{DS})$

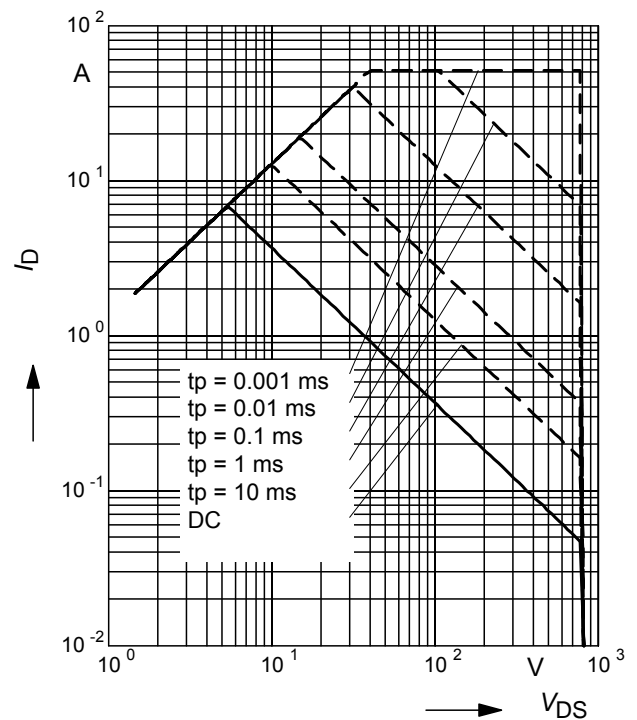
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



4 Safe operating area FullPAK

$I_D = f(V_{DS})$

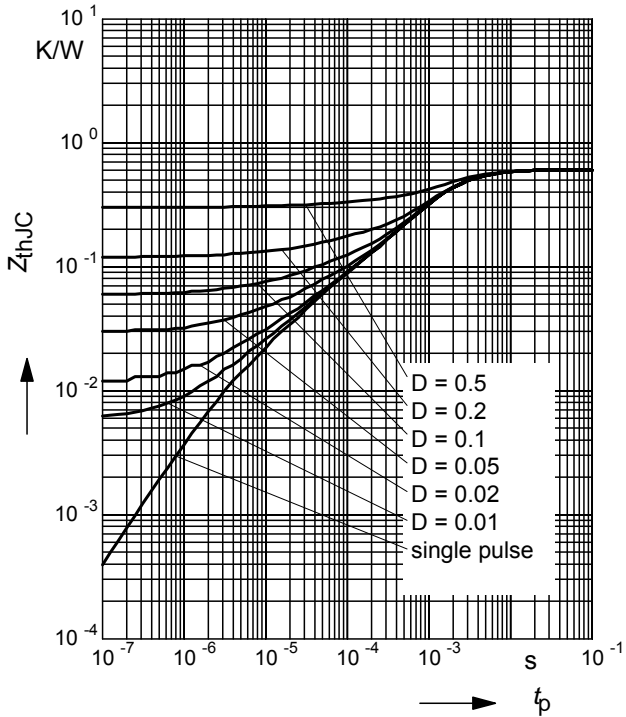
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



5 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

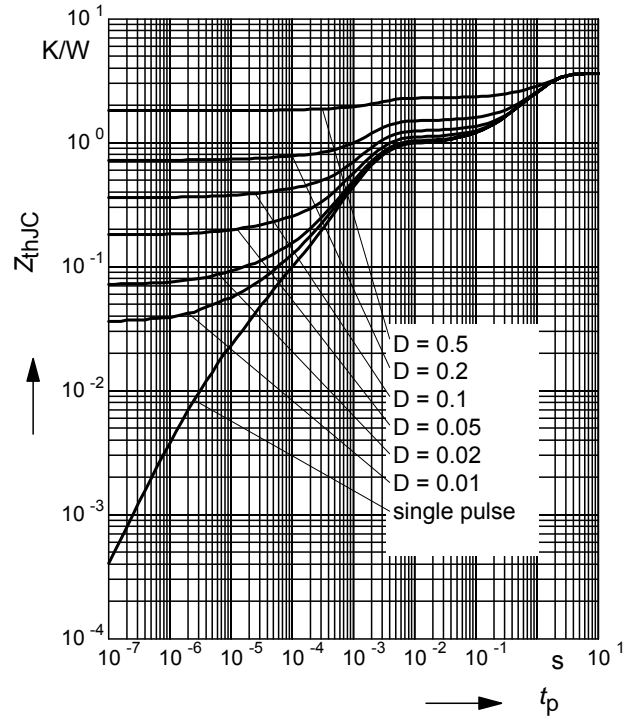
parameter: $D = t_p/T$



6 Transient thermal impedance FullPAK

$$Z_{thJC} = f(t_p)$$

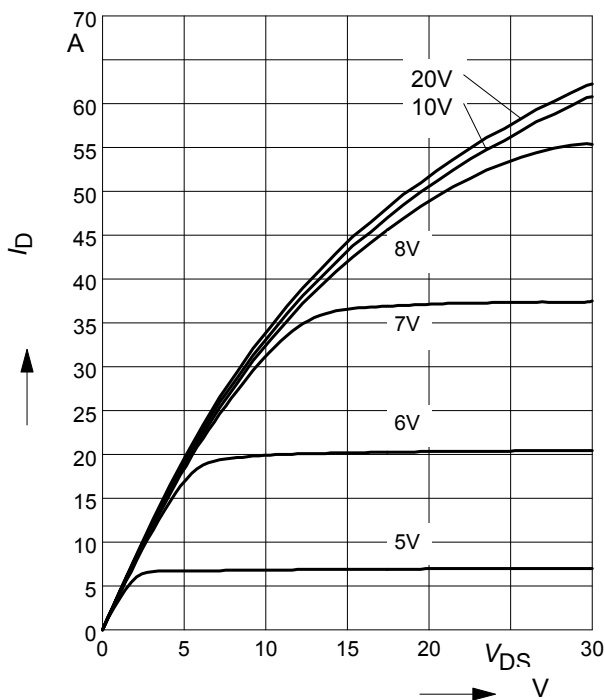
parameter: $D = t_p/t$



7 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

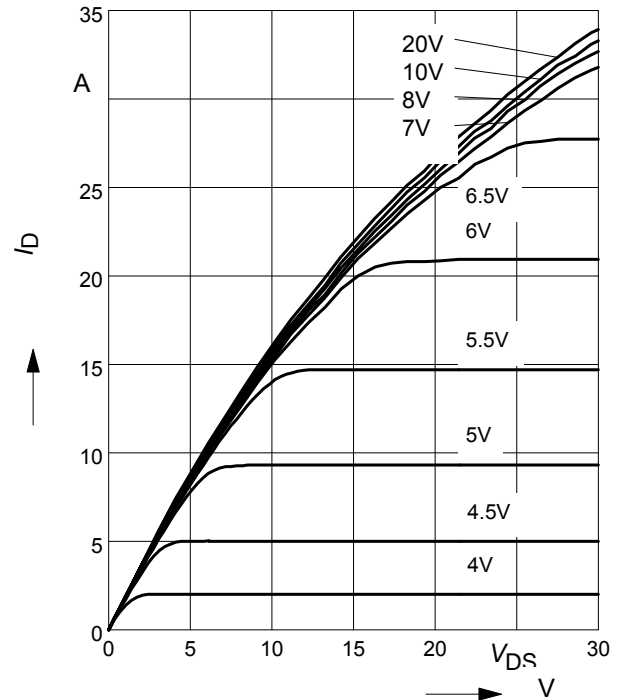
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



8 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

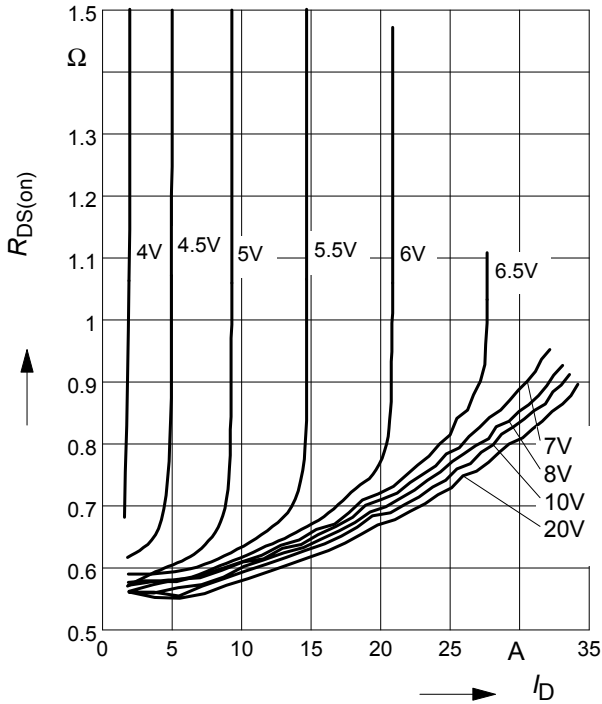
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



9 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

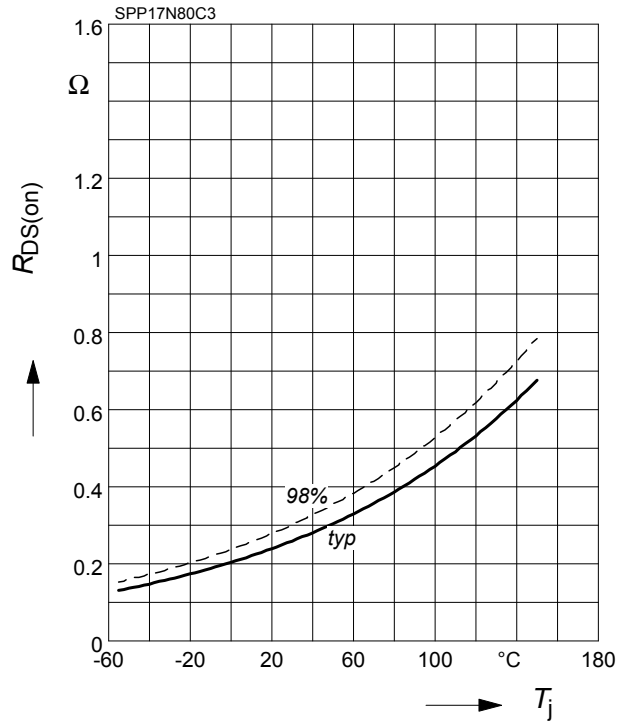
parameter: $T_j = 150^\circ\text{C}$, V_{GS}



10 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

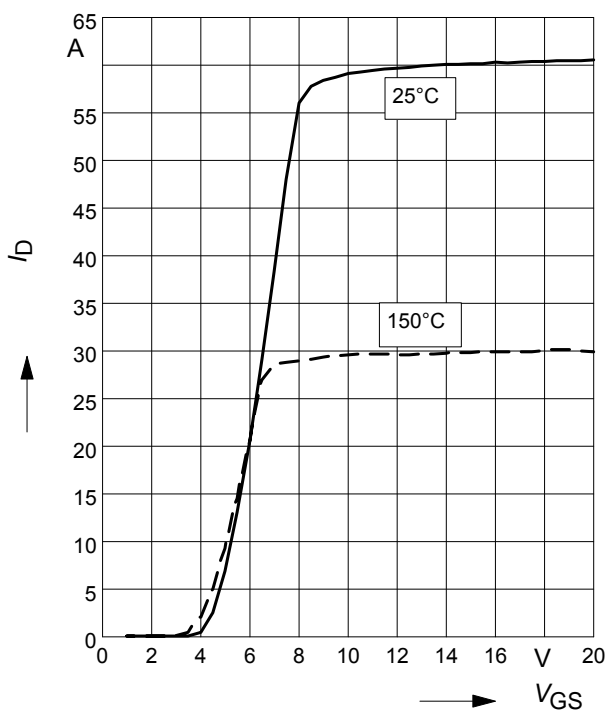
parameter: $I_D = 11\text{ A}$, $V_{GS} = 10\text{ V}$



11 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

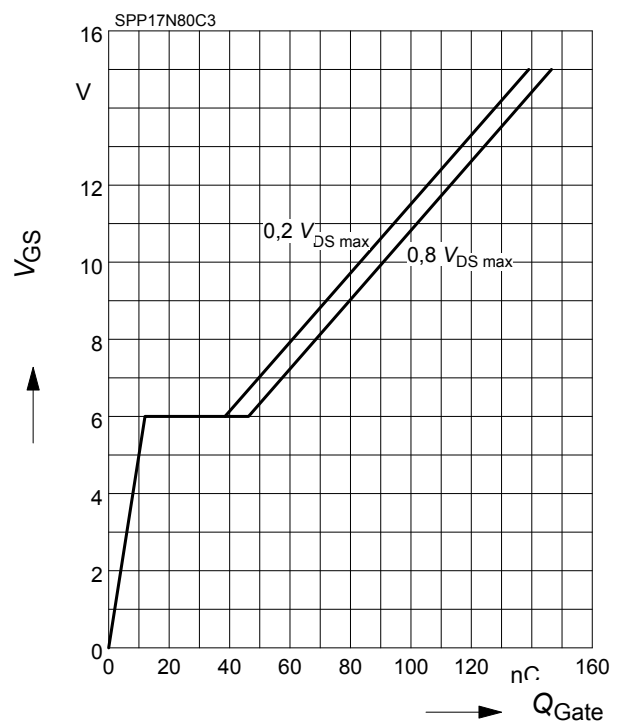
parameter: $t_p = 10\ \mu\text{s}$



12 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

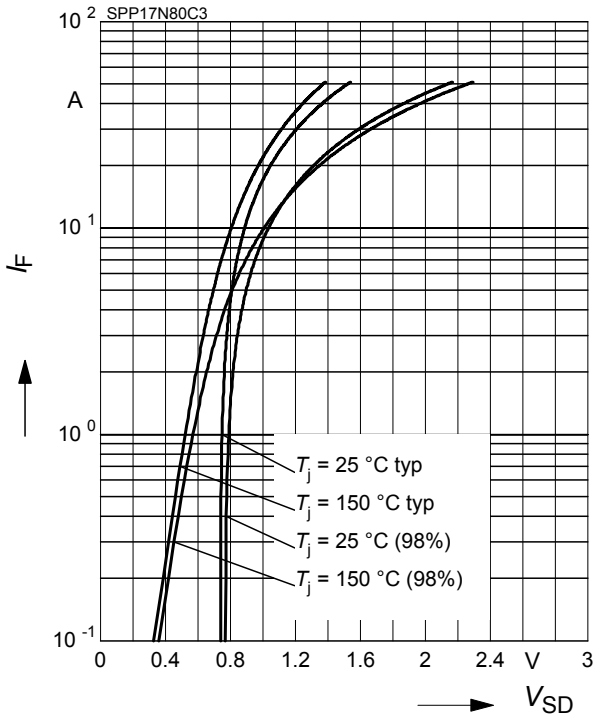
parameter: $I_D = 17\text{ A pulsed}$



13 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

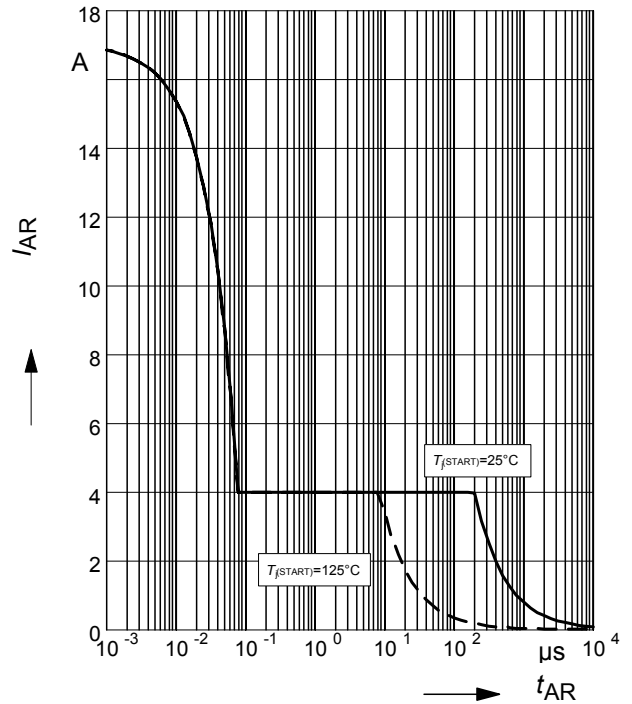
parameter: T_j , $t_p = 10 \mu s$



14 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

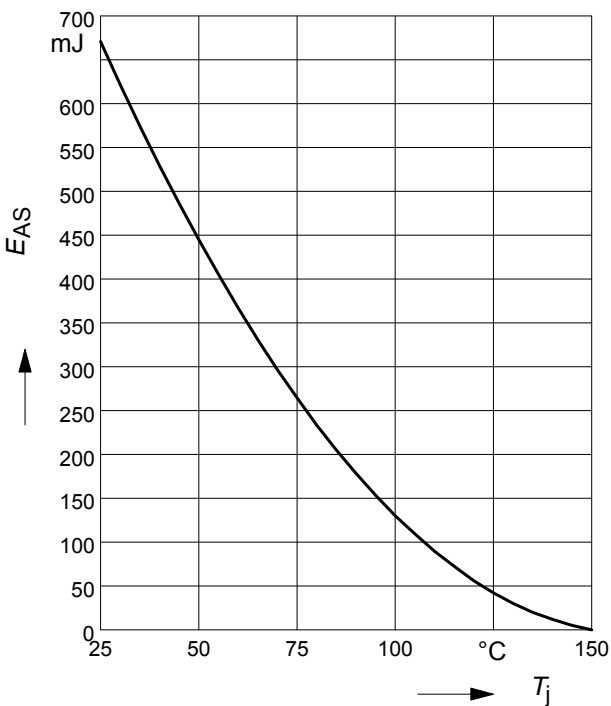
par.: $T_j \leq 150 \text{ °C}$



15 Avalanche energy

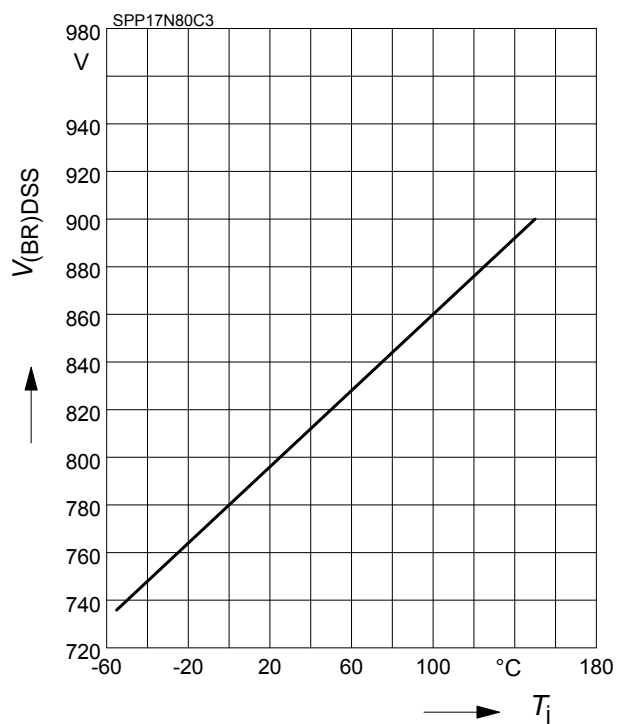
$$E_{AS} = f(T_j)$$

par.: $I_D = 3.4 \text{ A}$, $V_{DD} = 50 \text{ V}$



16 Drain-source breakdown voltage

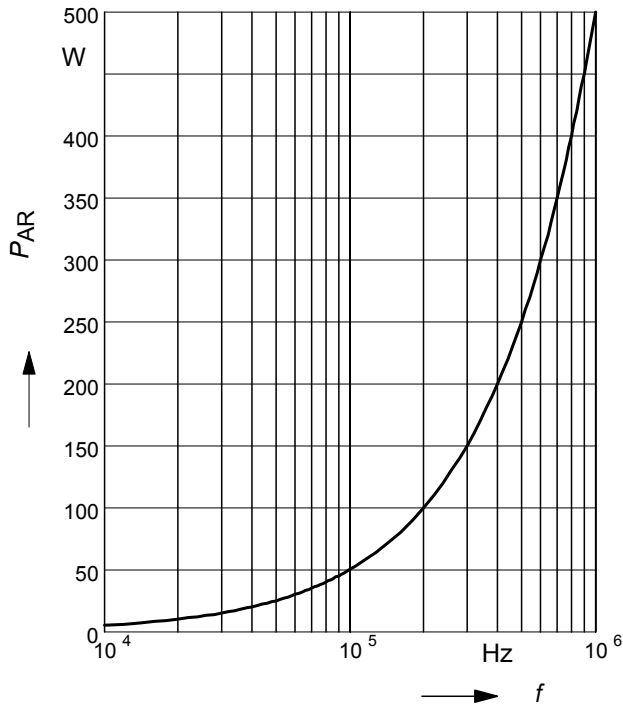
$$V_{(BR)DSS} = f(T_j)$$



17 Avalanche power losses

$$P_{AR} = f(f)$$

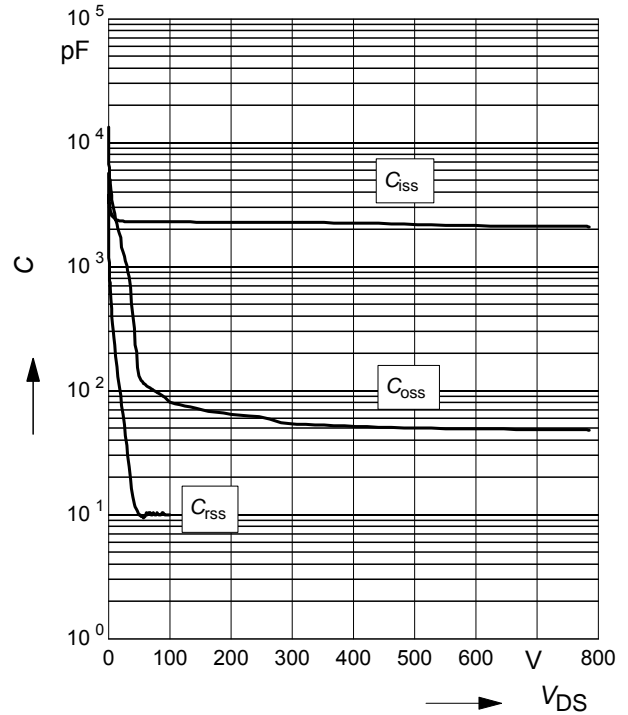
parameter: $E_{AR}=0.5\text{mJ}$



18 Typ. capacitances

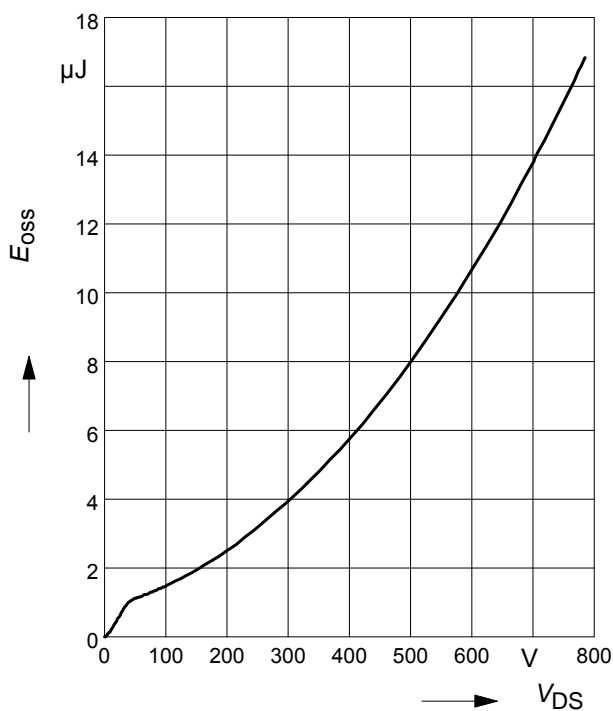
$$C = f(V_{DS})$$

parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$

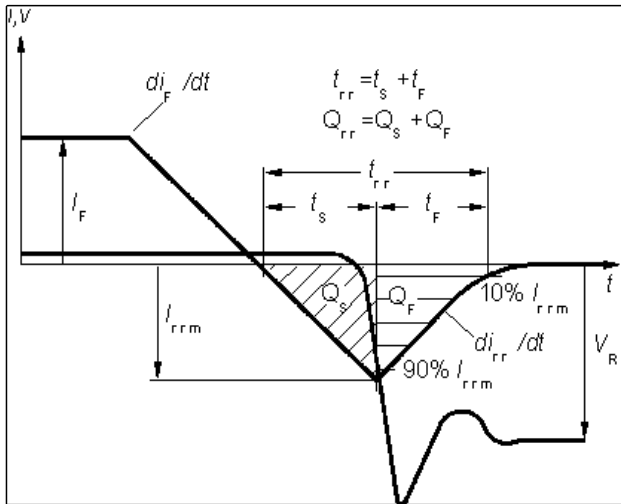


19 Typ. C_{oss} stored energy

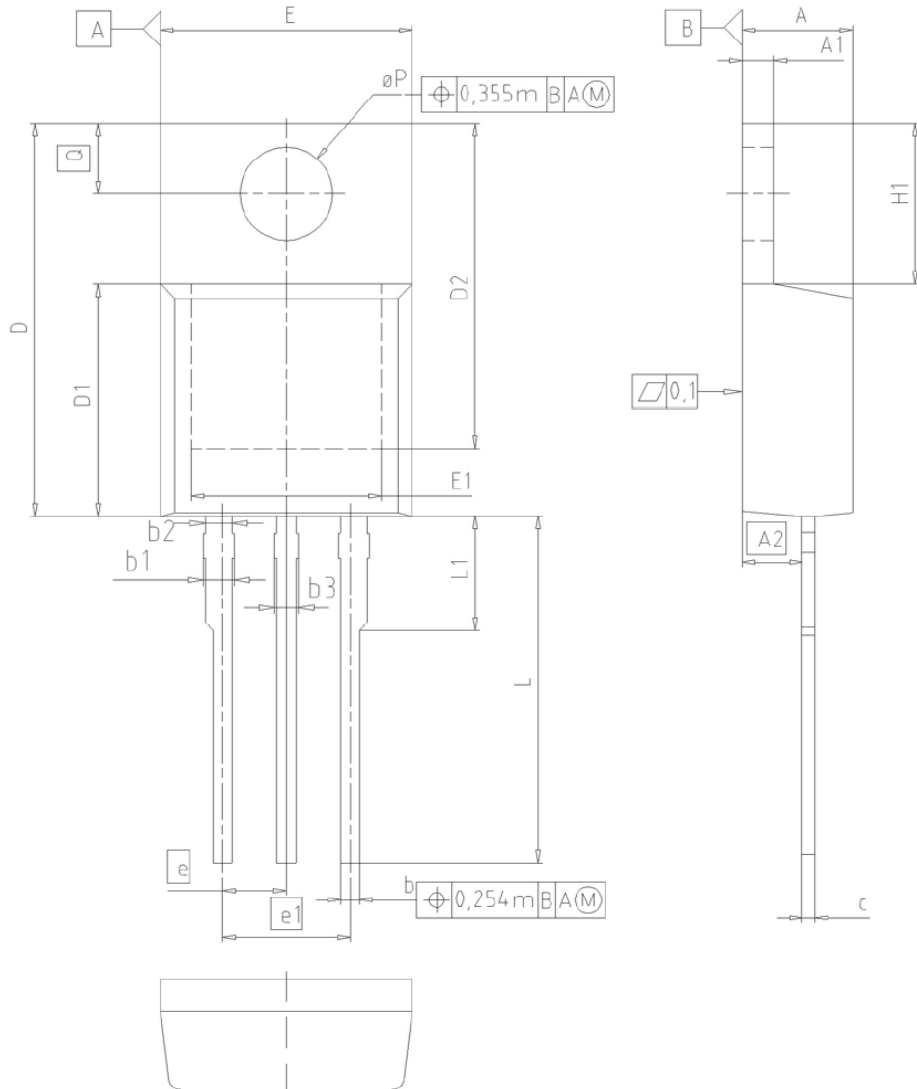
$$E_{Oss} = f(V_{DS})$$



Definition of diodes switching characteristics



PG-TO220-3-1, PG-TO220-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

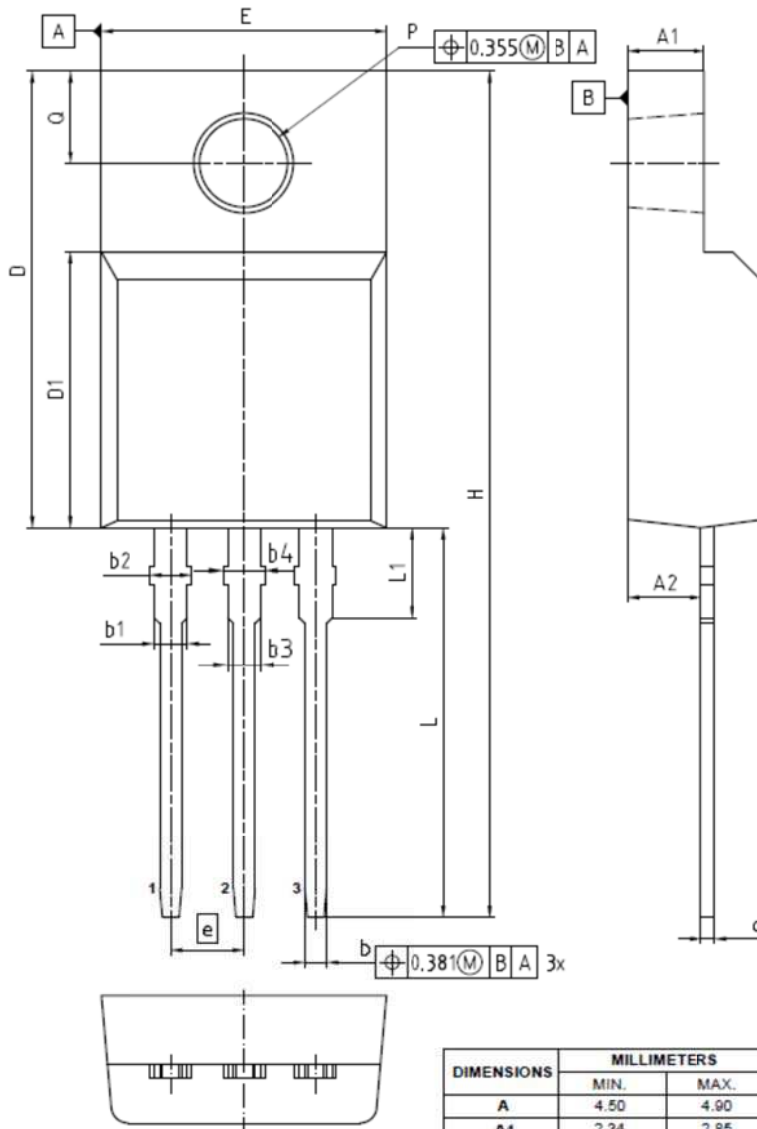
DOCUMENT NO.
Z8B00003318

SCALE

EUROPEAN PROJECTION

ISSUE DATE
23-08-2007

REVISION
05



NOTES:
ALL DIMENSIONS REFER TO JEDEC STANDARD TO-281
AND DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS
OR GATE BURRS
GATE BURRS ARE LESS THAN 0.5 nm

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.50	4.90
A1	2.34	2.85
A2	2.42	2.86
b	0.65	0.90
b1	0.95	1.38
b2	0.95	1.51
b3	0.65	1.38
b4	0.65	1.51
c	0.40	0.63
D	15.67	16.15
D1	8.97	9.83
E	10.00	10.65
e	2.54	
H	28.70	29.75
L	12.78	13.75
L1	2.83	3.45
eP	3.00	3.30
Q	3.15	3.50

DOCUMENT NO. Z8B00003319
REVISION 07
SCALE 5:1
EUROPEAN PROJECTION
ISSUE DATE 27.01.2017

Revision History

SPA17N80C3

Revision: 2017-07-27, Rev. 2.8

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.8	2017-07-27	Revised package drawing on page 12

Trademarks of Infineon Technologies AG

AURIX™, C166™, CanPAK™, CIPOS™, CoolGaN™, CoolMOS™, CoolSET™, CoolSiC™, CORECONTROL™, CROSSAVE™, DAVE™, DI-POL™, DrBlade™, EasyPIM™, EconoBRIDGE™, EconoDUAL™, EconoPACK™, EconoPIM™, EiceDRIVER™, eupec™, FCOS™, HITFET™, HybridPACK™, Infineon™, ISOFACE™, IsoPACK™, i-Wafer™, MIPAQ™, ModSTACK™, my-d™, NovalithIC™, OmniTune™, OPTIGA™, OptiMOS™, ORIGA™, POWERCODE™, PRIMARION™, PrimePACK™, PrimeSTACK™, PROFET™, PRO-SIL™, RASIC™, REAL3™, ReverSave™, SatRIC™, SIEGET™, SIPMOS™, SmartLEWIS™, SOLID FLASH™, SPOC™, TEMPFET™, thinQ!™, TRENCHSTOP™, TriCore™.

Trademarks updated August 2015

Other Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

erratum@infineon.com

Published by

Infineon Technologies AG

81726 München, Germany

© 2017 Infineon Technologies AG

All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.